

REWRITABLE MEMORY WITH NON-LINEAR MEMORY ELEMENT

Abstract

A re-writable memory that uses resistive memory cell elements with non-linear IV characteristics is disclosed. Non-linearity is important in certain memory arrays to prevent unselected cells from being disturbed and to reduce the required current. Non-linearity refers to the ability of the element to block the majority of current up to a certain level, but then, once that level is reached, the element allows the majority of the current over and above that level to flow.